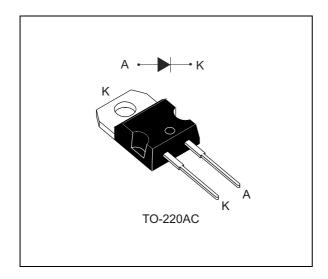


## STPSC6C065-Y

## Automotive 650 V power Schottky silicon carbide diode

Datasheet - production data



#### **Features**

- AEC-Q101 qualified
- No or negligible reverse recovery
- Switching behavior independent of temperature
- · Dedicated to PFC applications
- High forward surge capability

This is information on a product in full production.

- PPAP capable
- ECOPACK®2 compliant component

### **Description**

The SiC diode is an ultrahigh performance power Schottky diode. It is manufactured using a silicon carbide substrate. The wide band gap material allows the design of a Schottky diode structure with a 650 V rating. Due to the Schottky construction, no recovery is shown at turn-off and ringing patterns are negligible. The minimal capacitive turn-off behavior is independent of temperature and is ideal for automotive applications.

Especially suited for use as boost diode, this rectifier will enhance the performance in hard switching conditions. Its high forward surge capability ensures a good robustness during transient phases.

**Table 1. Device summary** 

,			
Symbol	Value		
I <sub>F(AV)</sub>	6 A		
$V_{RRM}$	650 V		
T <sub>j</sub> (max)	175 °C		

Characteristics STPSC6C065-Y

## 1 Characteristics

Table 2. Absolute ratings (limiting values at 25 °C unless otherwise specified)

Symbol	Par	Value	Unit	
$V_{RRM}$	Repetitive peak reverse voltage, T <sub>j</sub> = -40 °C		650	V
I <sub>F(RMS)</sub>	Forward rms current		22	Α
I <sub>F(AV)</sub>	Average forward current	$T_{c} = 135  ^{\circ}C^{(1)},  DC$	6	Α
I <sub>FSM</sub>	Surge non repetitive forward current	$t_p$ = 10 ms sinusoidal, $T_c$ = 25 °C $t_p$ = 10 ms sinusoidal, $T_c$ = 125 °C $t_p$ = 10 μs square, $T_c$ = 25 °C	49 43 375	A
I <sub>FRM</sub>	Repetitive peak forward current $T_c = 135  ^{\circ}C^{(1)}, T_j = 175  ^{\circ}C, \delta = 0.1$		25	Α
T <sub>stg</sub>	Storage temperature range		-65 to +175	°C
Tj	Operating junction temperature	-40 to +175	°C	

<sup>1.</sup> Value based on  $R_{th(j-c)}$  max.

Table 3. Thermal resistance

Symbol	Parameter	Val	Unit	
Symbol	rarameter	Тур.	Max.	Offic
R <sub>th(j-c)</sub>	Junction to case	1.95	2.6	°C/W

**Table 4. Static electrical characteristics** 

Symbol	Parameter	Tests conditions		Min.	Тур.	Max.	Unit
I <sub>R</sub> <sup>(1)</sup>	Reverse leakage current	T <sub>j</sub> = 25 °C	\/ -\/	-	5	60	μA
IR V Reverse leakage current	T <sub>j</sub> = 150 °C	$V_R = V_{RRM}$	-	50	250	μΑ	
V <sub>F</sub> <sup>(2)</sup>	V <sub>F</sub> <sup>(2)</sup> Forward voltage drop	T <sub>j</sub> = 25 °C	1 -61	-	1.56	1.75	V
VE V Forward Voltage drop	T <sub>j</sub> = 150 °C	I <sub>F</sub> = 6 A	-	1.98	2.5	V	

<sup>1.</sup>  $t_p = 10 \text{ ms}, \delta < 2\%$ 

To evaluate the conduction losses use the following equation:

$$P = 1.35 \text{ x } I_{F(AV)} + 0.192 \text{ x } I_{F^2(RMS)}$$

<sup>2.</sup>  $t_p = 500 \ \mu s, \ \delta < 2\%$ 

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Table 5. Dynamic electrical characteristics

Symbol	Parameter	Test conditions	Тур.	Unit
Q <sub>cj</sub> <sup>(1)</sup>	Total capacitive charge	V <sub>R</sub> = 400 V	15.2	nC
Ci	Total capacitance	$V_R = 0 \text{ V}, T_c = 25 \text{ °C}, F = 1 \text{ MHz}$	270	pF
C <sub>j</sub> Total capacitance		$V_R = 300 \text{ V}, T_C = 25 \text{ °C}, F = 1 \text{ MHz}$	29	рг

<sup>1.</sup> Most accurate value for the capacitive charge:  $Q_{cj} = \int_0^{V_{OUT}} c_j(v_R).dv_R$ 



Characteristics STPSC6C065-Y

Figure 1. Forward voltage drop versus forward current (typical values, low level)

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Pulse test: tp = 500 µs

T = 100 °C

T = 175 °C

T = 175 °C

Figure 2. Forward voltage drop versus forward current (typical values, high level) Pulse test: t<sub>p</sub> = 500 μ 50 40 30 T = 100 °C 20 10 0 0.0 1.0 2.0 3.0 4.0 5.0 6.0 7.0 8.0

Figure 3. Reverse leakage current versus reverse voltage applied (typical values)

1.5

2.0

2.5

0.5

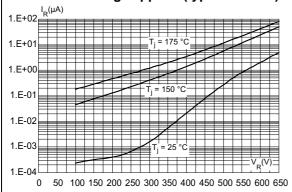


Figure 4. Peak forward current versus case temperature 70 60 40  $\delta = 0.3$ 30 δ = 0.5 20 10 T<sub>C</sub>(°C) 0 \_ 50 75 100 125 150 175

Figure 5. Junction capacitance versus reverse voltage applied (typical values)

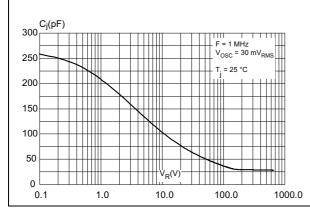
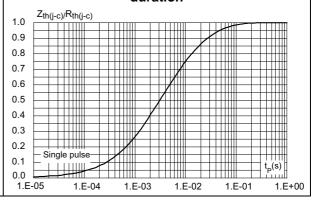


Figure 6. Relative variation of thermal impedance junction to case versus pulse duration



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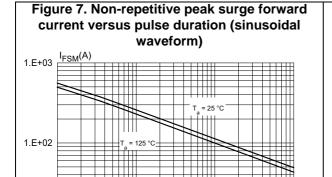
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t<sub>p</sub>(s)

1.E-02

1.E-03



1.E-04

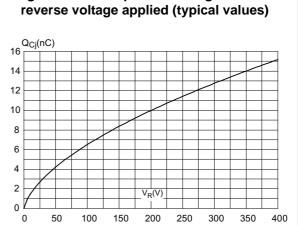


Figure 8. Total capacitive charges versus



1.E+01

1.E-05

Package information STPSC6C065-Y

## 2 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK<sup>®</sup> packages, depending on their level of environmental compliance. ECOPACK<sup>®</sup> specifications, grade definitions and product status are available at: <a href="https://www.st.com">www.st.com</a>. ECOPACK<sup>®</sup> is an ST trademark.

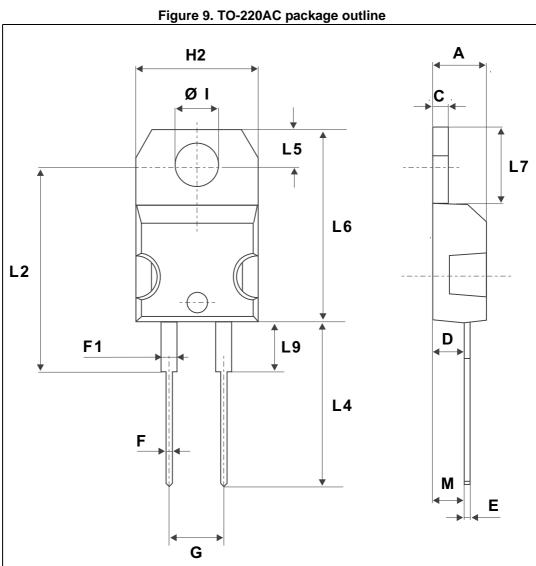
• Epoxy meets UL94, V0

Cooling method: by conduction (C)

• Recommended torque value: 0.55 N·m

Maximum torque value: 0.7 N.m

### 2.1 TO-220AC package information



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Table 6. TO-220AC package mechanical data

			Dimer	nsions		
Ref.		Millimeters			Inches	
	Min.	Тур.	Max.	Min.	Тур.	Max.
А	4.40		4.60	0.173		0.181
С	1.23		1.32	0.048		0.051
D	2.40		2.72	0.094		0.107
E	0.49		0.70	0.019		0.027
F	0.61		0.88	0.024		0.034
F1	1.14		1.70	0.044		0.066
G	4.95		5.15	0.194		0.202
H2	10.00		10.40	0.393		0.409
L2		16.40 typ.			0.645 typ.	
L4	13.00		14.00	0.511		0.551
L5	2.65		2.95	0.104		0.116
L6	15.25		15.75	0.600		0.620
L7	6.20		6.60	0.244		0.259
L9	3.50		3.93	0.137		0.154
М		2.6 typ.			0.102 typ.	
Diam. I	3.75		3.85	0.147		0.151

Ordering information STPSC6C065-Y

# 3 Ordering information

**Table 7. Ordering information** 

Order code	Marking	Package	Weight	Base qty.	Delivery mode	
STPSC6C065DY	PSC6C065DY	TO-220AC	1.86 g	50	Tube	

# 4 Revision history

**Table 8. Document revision history** 

Date	Revision	Changes	
13-Jan-2015	1	First issue.	
13-Dec-2016	2	Updated Table 4.	

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